

L Number	Hits	Search Text	DB	Time stamp
3	8	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron NEAR5 reflect\$5) WITH (potential\$5 near3 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 07:57
10	2	("5425041").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 07:55
17	2	(semiconductor near laser) and ((strain or streses or tension) with (electron NEAR5 reflect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 08:01
24	2	("5251224").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/19 08:01
-	1156	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and barrier and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 12:57
-	93	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and barrier and electron and (clad\$5 near2 (medium or region or layer or film))) and reflect\$5 and (potential near2 barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 12:48
-	5	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and barrier and electron and (clad\$5 near2 (medium or region or layer or film))) and ((electron near3 reflect\$5) WITH (potential near2 barrier))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 12:50
-	5	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) WITH (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:06
-	6	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and barrier and electron and (clad\$5 near2 (medium or region or layer or film))) and ((electron near3 reflect\$5) same (potential near2 barrier))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 15:59
-	1	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and barrier and electron and (clad\$5 near2 (medium or region or layer or film))) and ((electron near3 reflect\$5) same (potential near2 barrier))) not ((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) WITH (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 15:59
-	6	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) SAME (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:08
-	24	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) AND (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:54

-	18	((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) AND (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))) not ((semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near3 reflect\$5) SAME (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:29
-	10	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron WITH reflect\$5) WITH (potential near3 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:54
-	26	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near5 reflect\$5) AND (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 16:58
-	7	(semiconductor near laser) and ((active or gain) near2 (medium or region or layer or film)) and ((electron near5 reflect\$5) with (potential near2 barrier)) and electron and (clad\$5 near2 (medium or region or layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/18 17:03